

1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-51049-B

2. Structure :

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold .

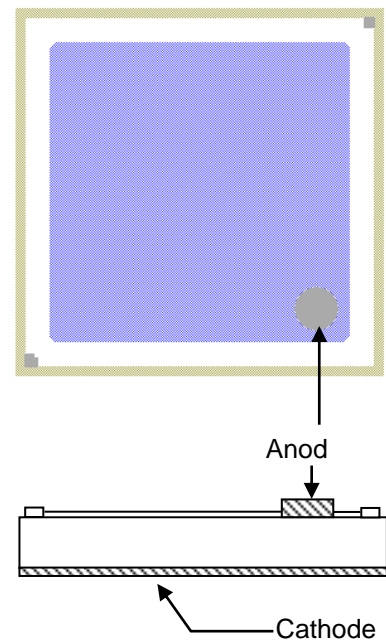
3. Size :

- 3-1. Chip size : 48.4 mils x 48.4 mils (1.230 mm x 1.230 mm).
- 3-2. Chip thickness : 8.66 ± 0.59 mils (0.220 ± 0.015 mm).
- 3-3. Active area : 39.4 mils x 39.4 mils (1.000 mm x 1.000 mm).
- 3-4. Bonding pad (Anode) : 5.5 mils (0.140 ± 0.010 mm) Diameter.
- 3-5. Pattern drawing : Refer to the attached drawing

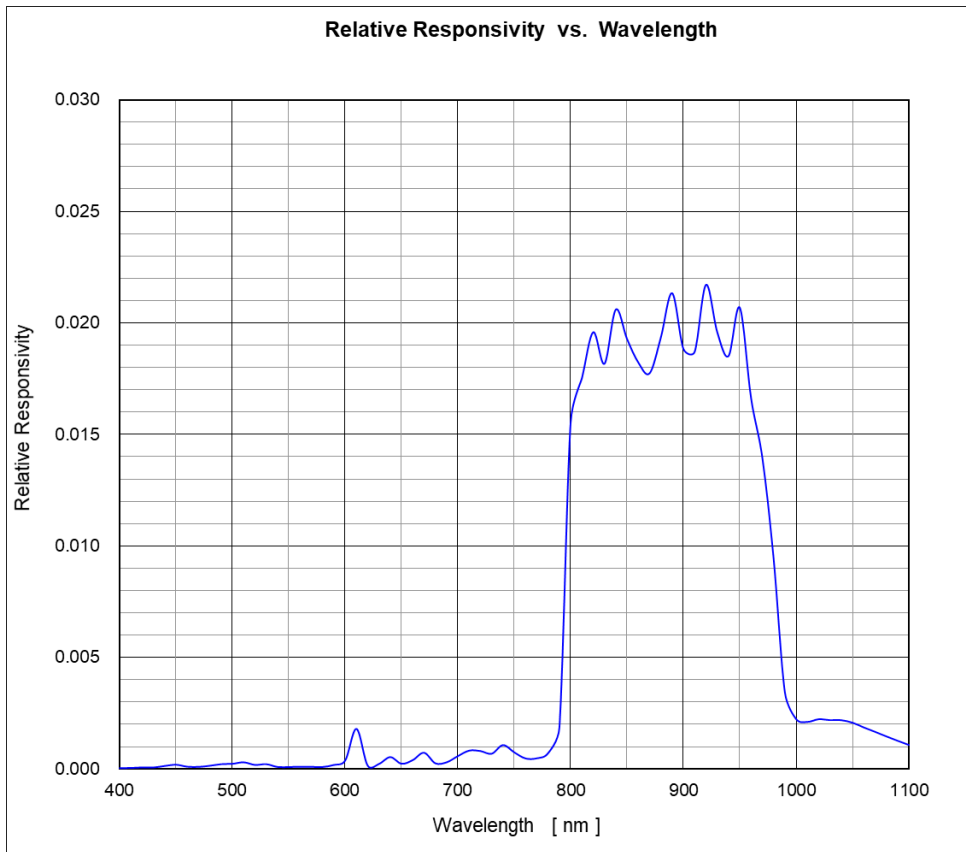
4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark Current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Forward Voltage	VF	$I_F=20mA$ $E_e=0mW/cm^2$			1.2	V

*Based on 100% probing



5. Relative spectral responsivity



※bare chip measured without integrating sphere, for reference only.